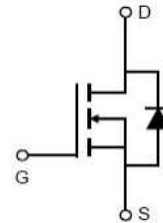




1. Description

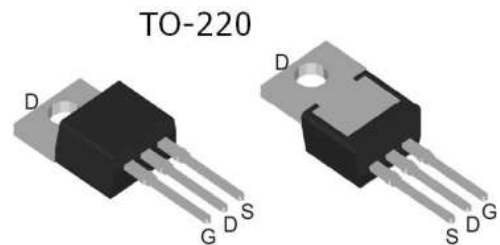
SS039N10TS, the N-channel Enhanced Power MOSFETs, is obtained by advanced double trench technology which reduce the conduction loss, improve switching performance and enhance the avalanche energy. This is suitable device for motor drivers and high speed switching applications.

Schematic Diagram



KEY CHARACTERISTICS

| Parameter | Value | Unit |
|------------------|-------|------|
| V_{DS} | 100 | V |
| I_D | 135 | A |
| $R_{DS(on).typ}$ | 3.3 | mΩ |



FEATURES:

- Fast Switching
- Low On-Resistance ($R_{DS(on)} \leq 3.9m\Omega$)
- Low Gate Charge
- Low Reverse transfer capacitances
- High avalanche ruggedness
- RoHS product

APPLICATIONS:

- Switching applications
- Motor drivers
- BMS
- Synchronous rectification

ORDERING INFORMATION

| Ordering Codes | Package | Product Code | Packing |
|----------------|---------|--------------|---------|
| SS039N10TS | TO-220 | SS039N10TS | Tube |